TRANSISTOR (PNP) **Plastic-Encapsulate Transistor**

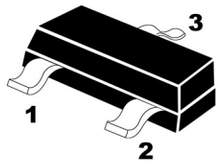
FEATURES

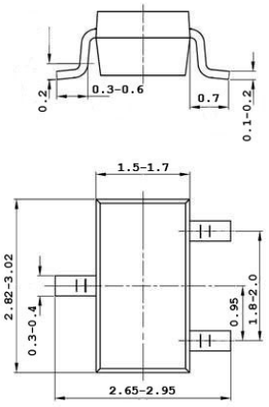
- Excellent h_{FE} linearity:
  $h_{FE(2)}$ = 25(min) at V_{CE} = -6V, I_C = -400mA
- High voltage: V_{CEO} = -50V(min)
- Complements the 2SC3325

MARKING: ACO, ACY

SOT-23-3L

1. BASE
2. EMITTER
3. COLLECTOR





Unit:mm

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25℃ ambient temperature unless otherwise specified.

MAXIMUM RATINGS

Parameters	Symbols	Value	UNITS
Collector-Base Voltage	V_{CBO}	-50	V
Collector-Emitter Voltage	V_{CEO}	-50	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current - Continuous	I_C	-500	mA
Base Current	I_B	-50	mA
Collector Dissipation	P_C	200	mW
Junction and Storage Temperature	T_J, T_{stg}	-55-150	℃

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

ELECTRICAL CHARACTERISTICS

Parameters	Symbol	Test conditions		MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C=-100μA, I_E=0		-50			V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=-1mA, I_B=0		-50			V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=-100μA, I_C=0		-5			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=-50V, I_E=0				-0.1	μA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=-5V, I_C=0				-0.1	μA
DC Current Gain	$h_{FE(1)}$ $h_{FE(2)}$	V_{CE}=-1V, I_C=-100mA V_{CE}=-6V, I_C=-400mA	 O Y	70 25 40		240	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=-100mA, I_B=-10mA				-0.25	V
Base-Emitter Voltage	V_{BE}	V_{CE}=-1V, I_C=-100mA				-1	V
Transition Frequency	f_T	V_{CE}=-6V, I_C=-20mA			200		MHz
Collector Output Capacitance	C_{ob}	V_{CB}=-6V, I_E=0, f=1MHz			13		pF

CLASSIFICATION OF $h_{FE(1)}$

Rank	O	Y
Range	70-140	120-240

RoHS Pb-free TIP Semiconductor